

RIDGE WAVEGUIDE LASERGaAs Semiconductor Laser Diode
Fabry-Perot Laser**PRELIMINARY SPECIFICATION****RW Laser****EYP-RWL-1080-00080-0750-SOT01-0000****General Product Information**

Product	Application
1080 nm Fabry-Perot Laser	Spectroscopy
sealed SOT Housing	
Monitor Diode	

Absolute Maximum Ratings

	Symbol	Unit	min	typ	max
Storage Temperature	T_S	°C	-20		85
Operational Temperature at Case	T_C	°C	-20		50
Forward Current	I_F	mA			150
Reverse Voltage	V_R	V			0
Output Power	P_{opt}	mW			90

Recommended Operational Conditions

	Symbol	Unit	min	typ	max
Operational Temperature at case	T_C	°C	15		40
Forward Current	I_F	mA			130
Output Power	P_{opt}	mW	10		80

Characteristics at $T_{amb} 25\text{ °C}$ at Begin Of Life

Parameter	Symbol	Unit	min	typ	max
Center Wavelength	λ_c	nm	1070	1080	1090
Spectral Width (FWHM)	$\Delta\lambda$	nm			1
Temperature Coefficient of Wavelength	$d\lambda / dT$	nm / K		0.3	
Output Power @ $I_F = 130\text{ mA}$	P_{opt}	mW	80		
Slope Efficiency	η_d	W / A	0.6	0.8	1.2
Threshold Current	I_{th}	mA			70



Stress in excess of the Absolute Maximum Ratings can cause permanent damage to the device. Operation at the Absolute Maximum Rating for extended periods of time can adversely affect the device reliability and may lead to reduced operational life.

Measurement Conditions / Comments

total output measured with integrating sphere

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Parameter	Symbol	Unit	min	typ	max
Operational Current @ $P_{opt} = 80$ mW	I_{op}	mA			130
Cavity Length	L	μm		750	
Divergence parallel (FWHM)	$\Theta_{ }$	$^{\circ}$		10	
Divergence perpendicular (FWHM)	Θ_{\perp}	$^{\circ}$		30	
Polarization				TE	
Spatial Mode (transversal)				TEM_{00}	
Spectral Mode (longitudinal)				Single/Multi Mode	

Measurement Conditions / Comments

E field parallel to Pin 2 - Pin 3 - plane

Fundamental Mode

depending on operating conditions

Monitor Diode

Parameter	Symbol	Unit	min	typ	max
Monitor Detector Responsivity	I_{mon} / P_{opt}	$\mu\text{A} / \text{mW}$	1		10
Reverse Voltage Monitor Diode	$U_{R,MD}$	V	3		5

Measurement Conditions / Comments

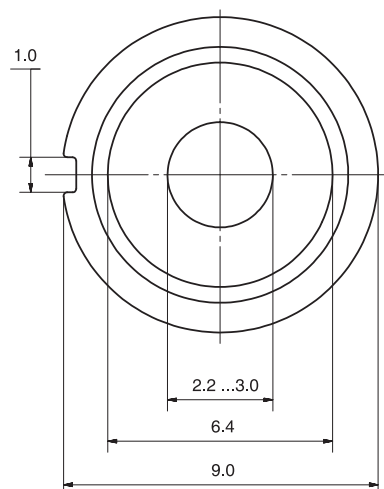
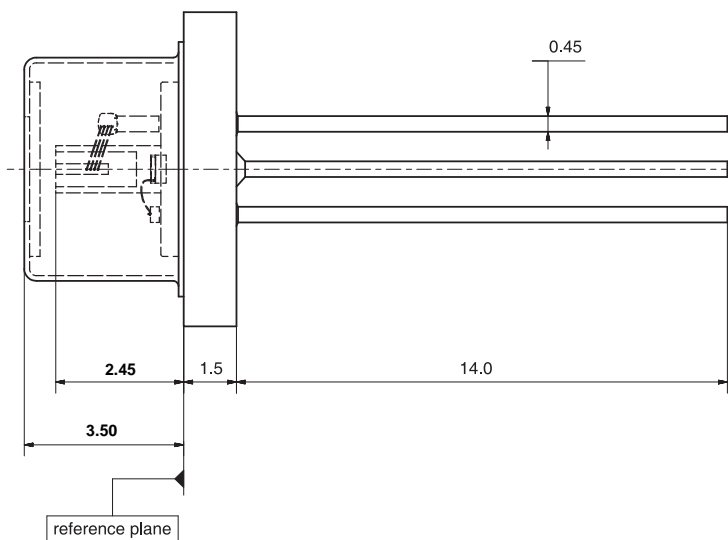
 $U_R = 5$ V, target values

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Fabry-Perot Laser**PRELIMINARY SPECIFICATION****EYP-RWL-1080-00080-0750-SOT01-0000****Package Dimensions**

	Symbol	Unit	min	typ	max
Height of Emission Plane	d_{EP}	mm	2.30	2.45	2.50
Excentricity of Emission Center	R	mm			0.12
Pin Length	l	mm		14.0	

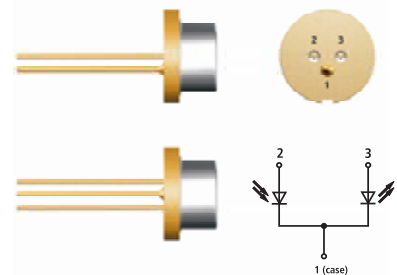
Package Pinout**M-Type**

Ground	1
Photo Diode (+)	2
Laser (+)	3

Package Drawings**RW Laser**

reference plane: top side of TO header

reference: center of outer diameter of header



RIDGE WAVEGUIDE LASER

GaAs Semiconductor Laser Diode
Fabry-Perot Laser



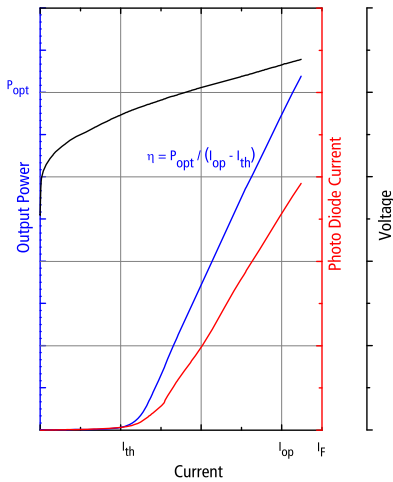
PRELIMINARY SPECIFICATION

RW Laser

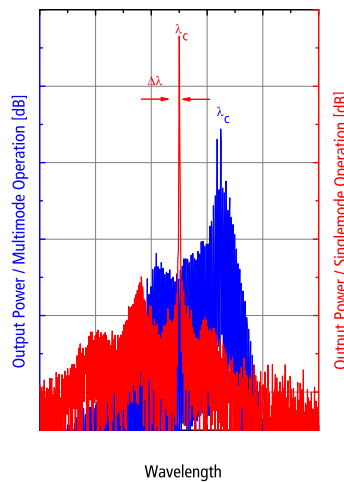
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Typical Measurement Results

Output Power vs. Current



Spectra at Specified Optical Output Power



Ordering Information:



800 Village Walk #316
Guilford, CT 06437
Ph: 203-401-8093

Email orders to: sales@xsoptix.com
Fax orders to: 800-878-7282

Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.

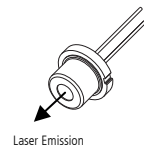
Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.

The RWL diode type is known to be sensitive against thermal stress. Operating at moderate temperatures on proper heat sinks will contribute to a long lifetime of the diode.

The laser emission from this diode is close to the invisible infrared region of the electromagnetic spectrum. Avoid direct and/or indirect exposure to the free running beam. Collimating the free running beam with optics as common in optical instruments will increase threat to the human eye.

Each laser diode will come with an individual test protocol verifying the parameters given in this document.



Complies with 21 CFR 1040.10 and 1040.40

